



# Product data sheet

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PESDUC2FD5VB-MSHF

Semiconductor Compiance

## **PIN CONFIGURATION**





DFN1006

## Features

- 100Watts peak pulse power (tp =  $8/20\mu s$ )
- Tiny DFN1006 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.25pF typ. IO to IO)
- Protection one data/power line to:
- IEC 61000-4-2 ±20kV contact ±20kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20µs)

## Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

## **Mechanical Data**

- 0402
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## Electrical Parameters (TA = 25 °C unless otherwise noted)

Symbol	Parameter	
Ipp	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
V <sub>RWM</sub>	Working Peak Reverse Voltage	
Ir	Maximum Reverse Leakage Current @ VRWM	
VBR	Breakdown Voltage @ IT	
Iт	Test Current	



Note:.  $8/20\mu s$  pulse waveform.



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# Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	P <sub>PP</sub>	100	Watts
Peak Pulse Current ( $t_p = 8/20 \mu s$ ) (note1)	I <sub>pp</sub>	4.0	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	20 20	kV
Lead Soldering Temperature	T <sub>L</sub>	260(10seconds)	°C
Junction Temperature	$T_J$	-55 to + 125	°C
Storage Temperature	T <sub>stg</sub>	-55 to + 125	°C

## **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V <sub>RWM</sub>				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6.0			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =5V,Т=25°С			100	nA
Peak Pulse Current	$I_{PP}$	tp =8/20µs			4.0	А
Clamping Voltage	V <sub>C</sub>	Ipp=4A,tp=8/20µs			25	V
Junction Capacitance	Cj	IO to IO $V_R = 0V, f = 1MHz$		0.25	0.4	pF





#### Typical **Characteristics**

### Figure 1: Peak Pulse Power vs. Pulse Time



Figure3: Pulse Waveform









Figure 2: Power Derating Curve





Figure5: Negative Clamping voltage (TLP)





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## PACKAGE MECHANICAL DATA



Dim	Inches		Millimeters		
	MIN	MAX	MIN	МАХ	
А	0.0125	0.02	0.32	0.52	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
н	0.015Typ.		0.40	Тур.	
R	0.001	0.005	0.05	0.15	

## **Suggested Pad Layout**



NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY.
  - CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

## **REEL SPECIFICATION**

P/N	PKG	QTY
PESDUC2FD5VB-MS	DFN1006	10000



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